

PROCEEDINGS OF SPIE

# ***Gallium Nitride Materials and Devices XVI***

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**6–11 March 2021**  
**Online Only, United States**

*Sponsored and Published by*  
SPIE

**Volume 11686**

Proceedings of SPIE 0277-786X, V. 11686

SPIE is an international society advancing an interdisciplinary approach to the science and application of light.

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Author(s), "Title of Paper," in *Gallium Nitride Materials and Devices XVI*, edited by Hiroshi Fujioka, Hadis Morkoç, Ulrich T. Schwarz, Proceedings of SPIE Vol. 11686 (SPIE, Bellingham, WA, 2021) Seven-digit Article CID Number.

ISSN: 0277-786X

ISSN: 1996-756X (electronic)

ISBN: 9781510642072

ISBN: 9781510642089 (electronic)

Published by

**SPIE**

P.O. Box 10, Bellingham, Washington 98227-0010 USA

Telephone +1 360 676 3290 (Pacific Time) Fax +1 360 647 1445

[SPIE.org](http://SPIE.org)

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